

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11	(implant\$ with (nitrogen "N.sub. 2")) with (oxidat\$ oxidiz\$) with (different near2 thickness)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:21
L2	406	(implant\$ with (nitrogen "N.sub. 2")) with (gate adj (insulat\$ or oxide))	US-PGPUB; USPAT	OR	OFF	2005/05/28 17:21
L3	4	(implant\$ with (nitrogen "N.sub. 2")) same (different near2 thickness) same (sidewall spacer)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:21
L4	19	(implant\$ with (nitrogen "N.sub. 2")) with (different adj thickness) with (gate transistor)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:22
L5	16	(implant\$ with (nitrogen "N.sub. 2")) with (thick\$) with (sidewall)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:22
L6	77	((dop\$ implant\$) with (nitrogen "N.sub.2")) same (different near2 thickness)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:23
L7	271	((((dop\$ implant\$) with (different near2 thickness\$))) not (((dop\$ implant\$) with (nitrogen "N.sub. 2")) same (different near2 thickness\$))) and (sidewall or spacer)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:23
L8	4	(vertical near2 implant\$) same (sidewall or spacer) same (thicker thicknesses thickness thinner thick) same (oxidation oxidize oxidizing reoxidation oxidized reoxidized)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:24
L9	26	(implant\$ with (nitrogen "N.sub. 2")) and (different adj thickness)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 17:24
L10	18	((((differ differing different) near3 thickness) and (gate mosfet transistor fet) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	US-PGPUB; USPAT	OR	ON	2005/05/28 17:25
L11	46	((thick thickness thicknesses thicker thinner) and (spacer sidewall) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	US-PGPUB; USPAT	OR	ON	2005/05/28 17:25

L12	24	(vertical\$ near2 (dop\$ implant\$)) same ((sidewall or spacer) with (thicker thicknesses thickness thinner thick))and(oxidation oxidize oxidizing reoxidation oxidized reoxidized)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:26
L13	4	(vertical near2 implant\$) same (sidewall or spacer) same (thicker thicknesses thickness thinner thick) same (oxidation oxidize oxidizing reoxidation oxidized reoxidized)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:27
L14	21	(vertical\$ near2 (dop\$ implant\$)) same (sidewall or spacer) same (thicker thicknesses thickness thinner thick) same (oxidation oxidize oxidizing reoxidation oxidized reoxidized)	US-PGPUB; USPAT	OR	ON	2005/05/28 17:28
L15	795	1 2 3 4 5 6 7 8 9 10 11 12 13 14	US-PGPUB; USPAT	OR	ON	2005/05/28 17:28
L16	749	15 not (@ad>"20031203" or @rlad>"20031203")	US-PGPUB; USPAT	OR	ON	2005/05/28 18:05
L17	0	("2004/0127006").URPN.	USPAT	OR	OFF	2005/05/28 17:41
L18	17	(implant\$ with (nitrogen "N.sub. 2")) same ((oxidation oxidiz\$3) with (differ\$3 near2 thickness))	US-PGPUB; USPAT	OR	ON	2005/05/28 18:05
L19	16	18 not (@ad>"20031203" or @rlad>"20031203")	US-PGPUB; USPAT	OR	ON	2005/05/28 18:05